

Sample &

Buy







TPS7A37

ZHCSB77B - MARCH 2013 - REVISED AUGUST 2015

TPS7A37 具有反向电流保护功能的 1% 高精度、 1A 低压降稳压器

Technical

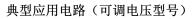
Documents

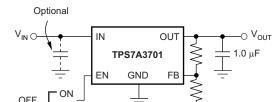
特性 1

- 与 1µF 或更大的陶瓷输出电容搭配工作时保持稳定
- 输入电压范围: 2.2V 至 5.5V
- 超低压降电压: •
 - 1A 时的最大电压为 200mV
- 出色的负载瞬态响应 即使与仅为 1µF 的输出电容 • 搭配使用也依旧出色
- NMOS 拓扑结构可提供低反向泄漏电流
- 出色的精度:
 - 0.23% 标称准确度
 - 整个线路、负载和温度范围内的总精度为 1%
- 关断模式下的 Io 典型值小于 20nA ٠
- 用于故障保护的热关断和电流限制 •

2 应用

- 针对数字信号处理器 (DSP),现场可编程栅极阵列 • (FPGA),特定用途集成电路 (ASIC) 和微处理器的 负载点调节
- 针对开关电源的后置调节
- 便携式和电池供电类设备 •





3 说明

7 Tools &

Software

TPS7A37 系列线性低压降 (LDO) 稳压器在一个电压随 耦器配置中使用一个 N 沟道金属氧化物半导体 (NMOS) 导通元件。该拓扑结构对输出电容值和等效串 联电阻 (ESR) 的敏感度相对较低,从而实现多种负载 配置。负载瞬态响应出色,即使与 1µF 小型陶瓷输出 电容搭配工作时也是如此。NMOS 拓扑结构也可实现 极低压降。

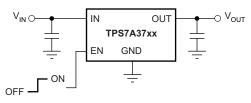
TPS7A37 系列使用一个先进的双极互补金属氧化物半 导体 (BiCMOS) 工艺,可在传送极低压降电压和低接 地引脚电流的同时产生高精度。未使能状态下的电流消 耗小于 20nA,非常适合便携式 应用。这些器件受到热 关断和折返电流限制的保护。

哭件信息(1)

器件型号	封装	封装尺寸(标称值)
TPS7A37	WSON (6)	2.00mm x 2.00mm

(1) 要了解所有可用封装,请见数据表末尾的可订购产品附录。

典型应用电路(固定电压型号)





目录

特性		8	Application and Implementation	14
应用			8.1 Application Information	14
	l		8.2 Typical Applications	
	历史记录	9	Power Supply Recommendations	19
	Configuration and Functions	10	Layout	19
	cifications		10.1 Layout Guidelines	19
6.1	Absolute Maximum Ratings 3		10.2 Layout Example	19
6.2	ESD Ratings		10.3 Thermal Considerations	20
6.3	Recommended Operating Conditions		10.4 Power Dissipation	20
6.4	Thermal Information		10.5 Estimating Junction Temperature	<mark>21</mark>
6.5	Electrical Characteristics5	11	器件和文档支持	
6.6	Typical Characteristics 6		11.1 文档支持	
	ailed Description 11		11.2 商标	23
7.1	Overview 11		11.3 静电放电警告	23
7.2	Functional Block Diagrams 11		11.4 Glossary	23
7.3	Feature Description 12	12	机械、封装和可订购信息	23
7.4	Device Functional Modes 13			

4 修订历史记录

1

2

3

4

5

6

7

注: 之前版本的页码可能与当前版本有所不同。

Cł	nanges from Revision A (July 2013) to Revision B	Page
•	已添加 ESD 额定值表,特性 描述部分,器件功能模式,应用和实施部分,电源相关建议部分,布局部分,器件和文 档支持部分以及机械、封装和可订购信息部分。	
•	Changed Internal Reference (VFB) parameter typ value	5
Cł	nanges from Original (March 2013) to Revision A	Page

onunges	ginai (ini		

•	已更改器件状态至"量产数据"	 1
_		_



www.ti.com.cn



5 Pin Configuration and Functions

C (
OUT	1	6	IN
NR/FB GND	3	4	N/C EN

Power dissipation may limit operating range. Check Thermal Information table.

Pin Functions

PIN NAME NO.		1/0	DESCRIPTION
		I/O	DESCRIPTION
EN	4	I	Driving the enable pin (EN) high turns on the regulator. Driving this pin low puts the regulator into shutdown mode. Refer to the <i>Shutdown</i> section under <i>Applications Information</i> for more details. EN must not be left floating and can be connected to IN if not used.
FB 2 I		I	Adjustable voltage version only—this pin is the input to the control loop error amplifier, and is used to set the output voltage of the device.
GND	3, Pad	_	Ground
IN	6	I	Unregulated input supply
N/C	5	—	Not connected
NR/FB	2	—	Fixed voltage versions only—connecting an external capacitor to this pin bypasses noise generated by the internal bandgap, reducing output noise to very low levels.
OUT 1 O		0	Regulator output. A 1.0-µF or larger capacitor of any type is required for stability.
PowerPAD	—		

6 Specifications

6.1 Absolute Maximum Ratings

Over operating temperature range (unless otherwise noted). $^{\left(1\right) }$

		MIN	MAX	UNIT
Voltage	IN	-0.3	6	V
	EN	-0.3	6	V
	OUT	-0.3	5.5	V
	NR, FB	-0.3	6	V
Current	Peak output current	Intern	Internally limited	
Current	Output short-circuit duration	In	definite	А
Temperature	Operating junction, T _J	-55	150	°C
	Storage, T _{stg}	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 $^{\left(2\right) }$	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
V _{IN}	2.2		5.5	V
V _{OUT}	V _{FB}		$5.5 - V_{DO}$	V
V _{EN}	0		V _{IN}	
Iout	0		1	А
C _{IN}		1		μF
C _{OUT} ⁽¹⁾	1			μF
C _{NR}		10		nF
R ₁ ⁽²⁾		V _{OUT(nom)} × 15.833		kΩ
C _{FF}		10	100	nF

(1) If the product of COUT x ESR < 50 n Ω -F, the part may ring after a transient.

(2) This nominal value is for the best accuracy.

6.4 Thermal Information

		TPS7A37	
	THERMAL METRIC ⁽¹⁾	DRV (WSON)	UNIT
		6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	67.2	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	87.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	36.8	°C/W
TυΨ	Junction-to-top characterization parameter	1.8	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	37.2	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	7.7	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

Over operating temperature range ($T_J = -40^{\circ}C$ to 125°C), $V_{IN} = V_{OUT(nom)} + 1 V^{(1)}$, $I_{OUT} = 10$ mA, $V_{EN} = 2.2$ V, and $C_{OUT} = 2.2 \mu$ F, unless otherwise noted. Typical values are at $T_J = 25^{\circ}C$.

	PARAMETE	R	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IN}	Input voltage ran	ge ⁽¹⁾⁽²⁾		2.2		5.5	V
V _{FB}	Internal reference	e	$T_J = 25^{\circ}C$	1.192	1.204	1.216	V
	Output voltage ra	ange	TPS7A3701 ⁽³⁾	V _{FB}		$5.5 - V_{DO}$	V
		Nominal	T _J = 25°C		0.23%		
V _{OUT}	Accuracy ^{(1), (4)}	over V _{IN} , I _{OUT} , and T _J = –40°C to 125°C	V _{OUT} + 0.5 V ≤ V _{IN} ≤ 5.5 V; 10 mA ≤ I _{OUT} ≤ 1 A	-1%		+1.0%	
$\Delta V_{O(\Delta VI)}$	Line regulation ⁽¹⁾		$V_{OUT(nom)} + 0.5 V \le V_{IN} \le 5.5 V$		0.01	0.03	%/V
					0.25%	0.35%	
$\Delta V_{O(\Delta IO)}$	Load regulation		0.1 mA ≤ I _{OUT} ≤ 300 mA		3	5	mV
()			10 mA ≤ I _{OUT} ≤ 1 A		0.5%		
V _{DO}	Dropout voltage ⁽ (V _{IN} = V _{OUT(nom)} -		I _{OUT} = 1 A		130	200	mV
Z _O (DO)	Output impedance	e in dropout	$2.2 \text{ V} \le \text{V}_{\text{IN}} \le \text{V}_{\text{OUT}} + \text{V}_{\text{DO}}$		0.25		Ω
I _{CL}	Output current lin	nit	$V_{OUT} = 0.9 \times V_{OUT(nom)}$	1.05	1.6	2.2	А
I _{SC}	Short-circuit curre	ent	V _{OUT} = 0 V		450		mA
I _{REV}	Reverse leakage	current ⁽⁶⁾ (-I _{IN})	$V_{EN} \le 0.5 \text{ V}, 0 \text{ V} \le V_{IN} \le V_{OUT}$		0.1		μA
			$I_{OUT} = 10 \text{ mA} (I_Q)$		400		۵
IGND	GND pin current		I _{OUT} = 1 A		1300		μA
I _{SHDN}	Shutdown curren	t (I _{GND})	$V_{EN} \le 0.5 \text{ V}, V_{OUT} \le V_{IN} \le 5.5 \text{ V}$		20		nA
I _{FB}	FB pin current		TPS7A3701		0.1	0.6	μA
	Power-supply rej	ection ratio (ripple	f = 100 Hz, I _{OUT} = 1 A		58		
PSRR	rejection)		f = 10 kHz, I _{OUT} = 1 A		37		dB
V _N	Output noise volt BW = 10 Hz to 10		C _{OUT} = 10 μF		27 × V _{OUT}		μV _{RMS}
t _{STR}	Startup time		V_{OUT} = 3 V, R_L = 30 Ω , C_{OUT} = 1 μ F		600		μs
V _{EN(HI)}	EN pin high (ena	bled)		1.7		V _{IN}	V
V _{EN(LO)}	EN pin low (shute	down)		0		0.5	V
I _{EN(HI)}	EN pin current (e	nabled)	V _{EN} = 5.5 V		20		nA
T	The second sheet 1		Shutdown, temperature increasing		160		*0
T _{SD}	Thermal shutdow	in temperature	Reset, temperature decreasing		140		°C
TJ	Operating junctio	n temperature		-40		125	°C

(1) Minimum $V_{IN} = V_{OUT} + V_{DO}$ or 2.2 V, whichever is greater. (2) For $V_{OUT(nom)} < 1.6$ V, when $V_{IN} \le 1.6$ V, the output will lock to V_{IN} and may result in an over-voltage condition on the output. To avoid this situation, disable the device before powering down VIN.

(3)

TPS7A3701 is tested at V_{OUT} = 1.2 V. Tolerance of external resistors not included in this specification. (4)

 V_{DO} is not measured for fixed output versions with $V_{OUT(nom)} < 2.3$ V since minimum $V_{IN} = 2.2$ V. Fixed-voltage versions only; refer to the *Application Information* section for more information. (5)

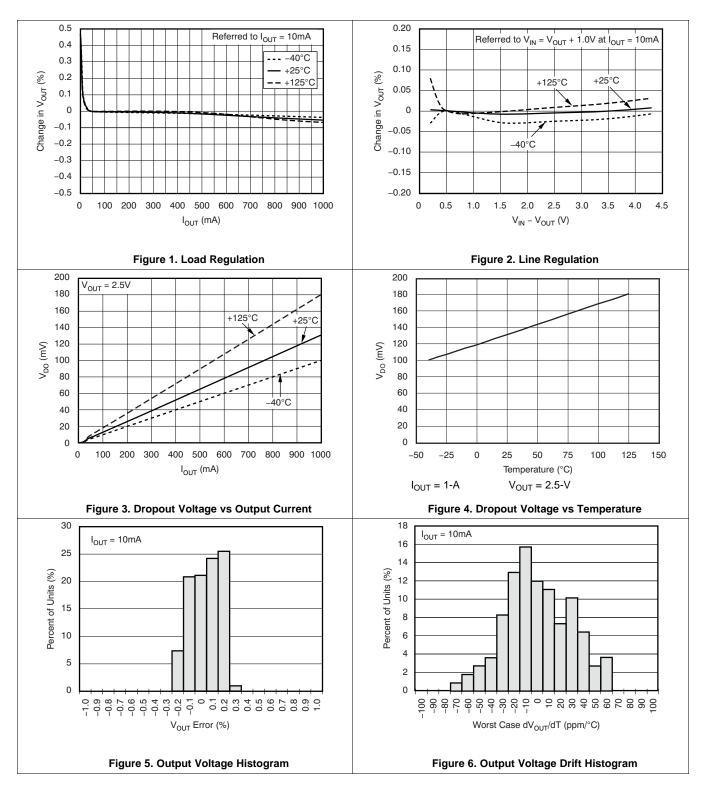
(6)

TPS7A37 ZHCSB77B – MARCH 2013 – REVISED AUGUST 2015



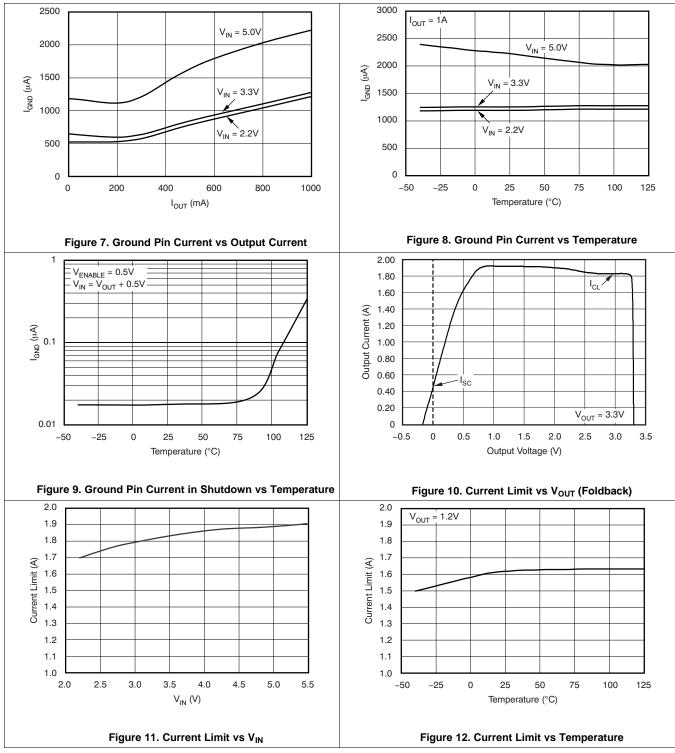
www.ti.com.cn

6.6 Typical Characteristics





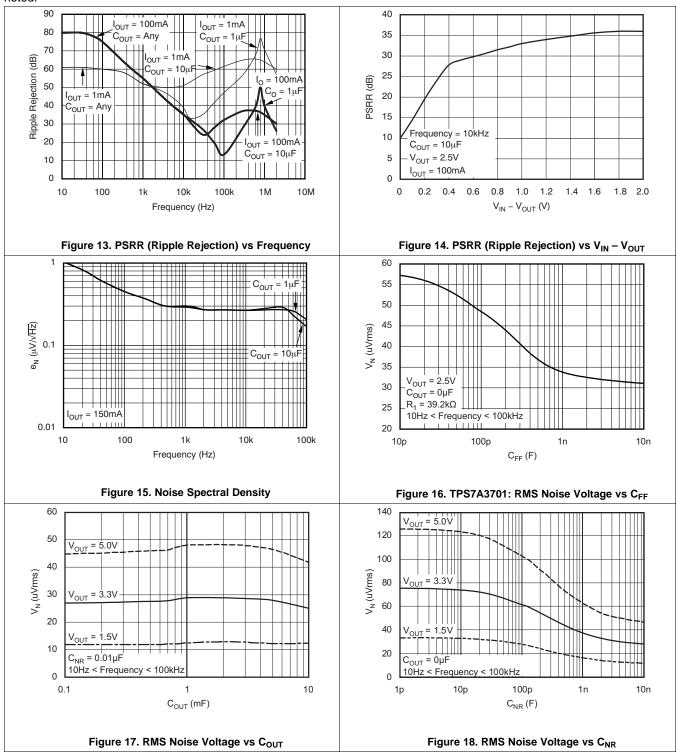
Typical Characteristics (continued)



TPS7A37 ZHCSB77B – MARCH 2013 – REVISED AUGUST 2015

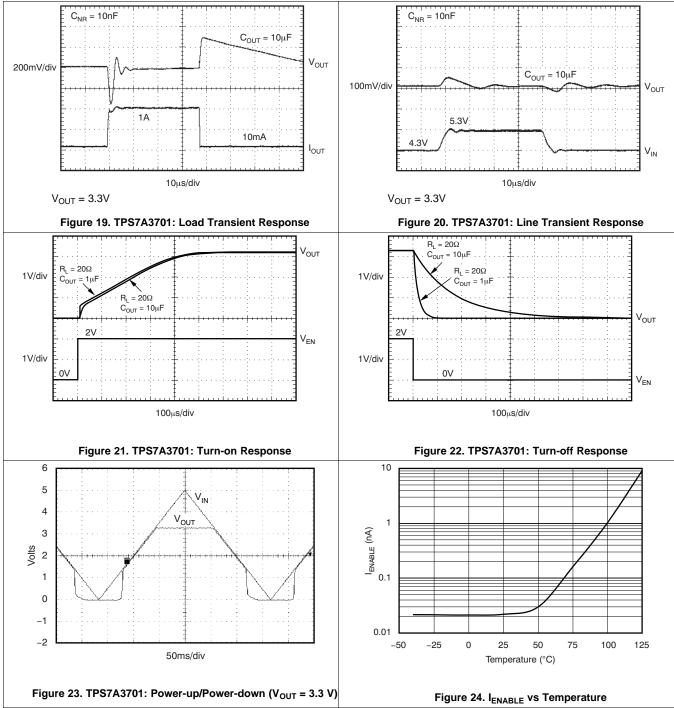
www.ti.com.cn

Typical Characteristics (continued)





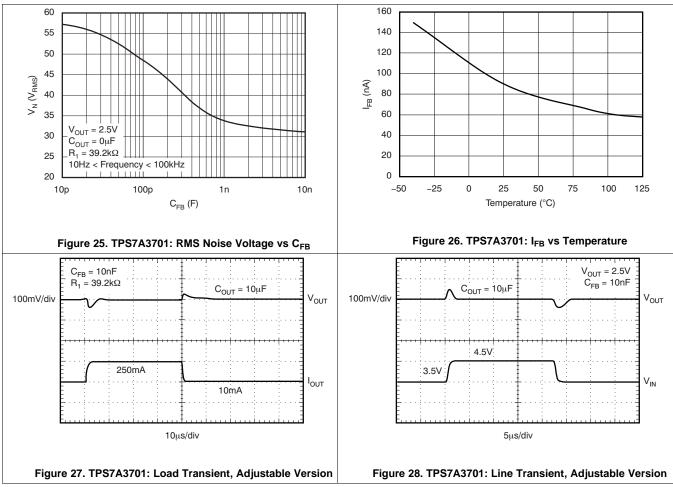
Typical Characteristics (continued)



TPS7A37 ZHCSB77B – MARCH 2013 – REVISED AUGUST 2015

www.ti.com.cn

Typical Characteristics (continued)



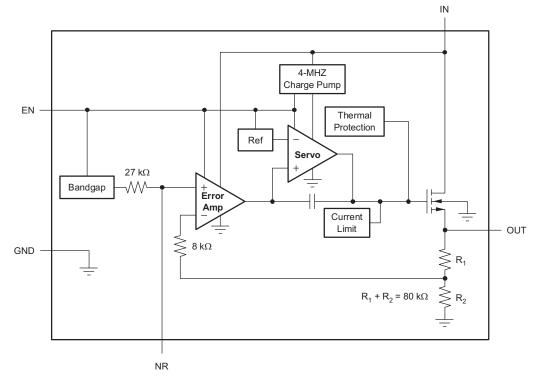


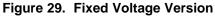
7 Detailed Description

7.1 Overview

The TPS7A37 belongs to a family of LDO regulators that use an NMOS pass transistor to achieve ultra-lowdropout performance and reverse current protection. These features combined with an enable input make the TPS7A37 ideal for portable applications. This regulator family offers a wide selection of fixed output voltage versions and an adjustable output version. All versions have thermal and over-current protection, including foldback current limit.

7.2 Functional Block Diagrams





Functional Block Diagrams (continued)

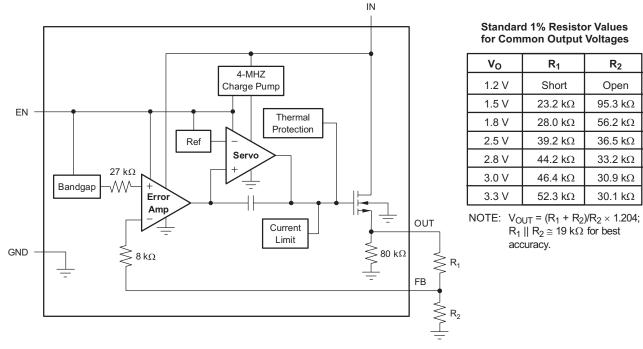


Figure 30. Adjustable Voltage Version

7.3 Feature Description

7.3.1 Internal Current Limit

The TPS7A37 internal current limit helps protect the regulator during fault conditions. Foldback current limit helps to protect the regulator from damage during output short-circuit conditions by reducing current limit when V_{OUT} drops below 0.5 V. See Figure 10 in the *Typical Characteristics* section.

Note from Figure 10 that approximately -0.2 V of V_{OUT} results in a current limit of 0 mA. Therefore, if OUT is forced below -0.2 V before EN goes high, the device may not start up. In applications that work with both a positive and negative voltage supply, the TPS7A37 should be enabled first.

7.3.2 Enable Pin and Shutdown

The enable pin (EN) is active high and is compatible with standard TTL-CMOS levels. A V_{EN} below 0.5 V (max) turns the regulator off and drops the GND pin current to approximately 10 nA. When EN is used to shutdown the regulator, all charge is removed from the pass transistor gate, and the output ramps back up to a regulated V_{OUT} (see Figure 21).

When shutdown capability is not required, EN can be connected to V_{IN} . However, the pass gate may not be discharged using this configuration, and the pass transistor may be left on (enhanced) for a significant time after V_{IN} has been removed. This scenario can result in reverse current flow (if the IN pin is low impedance) and faster ramp times upon power-up. In addition, for V_{IN} ramp times slower than a few milliseconds, the output may overshoot upon power-up.

Note that current limit foldback can prevent device start-up under some conditions. See the *Internal Current Limit* section for more information.



Feature Description (continued)

7.3.3 Reverse Current

The NMOS pass element of the TPS7A37 provides inherent protection against current flow from the output of the regulator to the input when the gate of the pass device is pulled low. To ensure that all charge is removed from the gate of the pass element, the EN pin must be driven low before the input voltage is removed. If this is not done, the pass element may be left on because of stored charge on the gate.

After the EN pin is driven low, no bias voltage is needed on any pin for reverse current blocking. Note that reverse current is specified as the current flowing out of the IN pin because of voltage applied on the OUT pin. There will be additional current flowing into the OUT pin as a result of the 80-k Ω internal resistor divider to ground (see Figure 29 and Figure 30).

For the TPS7A3701, reverse current may flow when V_{FB} is more than 1.0 V above V_{IN} .

7.4 Device Functional Modes

Driving the EN pin over 1.7 V turns on the regulator. Driving the EN pin below 0.5 V causes the regulator to enter shutdown mode. In shutdown, the current consumption of the device is reduced to 20 nA, typically.

INSTRUMENTS

www.ti.com.cn

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Input and Output Capacitor Requirements

Although an input capacitor is not required for stability if input impedance is very low, it is good analog design practice to connect a $0.1-\mu$ F to $1-\mu$ F low equivalent series resistance (ESR) capacitor across the input supply near the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated or the device is located several inches from the power source.

The TPS7A37 requires a 1- μ F output capacitor for stability. It is designed to be stable for all available types and values of capacitors. In applications where multiple low ESR capacitors are in parallel, ringing may occur when $C_{OUT} \times ESR < 50 \text{ n}\Omega$ -F. Total ESR includes all parasitic resistances, including capacitor ESR and board, socket, and solder joint resistance. In most applications, the sum of capacitor ESR and trace resistance will meet this requirement.

8.1.2 Output Noise

A precision bandgap reference is used to generate the internal reference voltage, V_{REF} . This reference is the dominant noise source within the TPS7A37 and it generates approximately 32 μV_{RMS} (10 Hz to 100 kHz) at the reference output (NR). The regulator control loop gains up the reference noise with the same gain as the reference voltage, so that the noise voltage of the regulator is approximately given by:

$$V_{N} = 32\mu V_{RMS} \times \frac{(R_1 + R_2)}{R_2} = 32\mu V_{RMS} \times \frac{V_{OUT}}{V_{REF}}$$
(1)

Since the value of V_{REF} is 1.2V, this relationship reduces to:

$$V_{N}(\mu V_{RMS}) = 27 \left(\frac{\mu V_{RMS}}{V}\right) \times V_{OUT}(V)$$
(2)

for the case of no C_{NR} .

An internal 27-k Ω resistor in series with the noise reduction pin (NR) forms a low-pass filter for the voltage reference when an external noise reduction capacitor, C_{NR} , is connected from NR to ground. For C_{NR} = 10 nF, the total noise in the 10-Hz to 100-kHz bandwidth is reduced by a factor of ~3.2, giving the approximate relationship:

$$V_{\rm N}(\mu V_{\rm RMS}) = 8.5 \left(\frac{\mu V_{\rm RMS}}{V}\right) \times V_{\rm OUT}(V)$$
(3)

for $C_{NR} = 10 \text{ nF}$.

This noise reduction effect is shown as RMS Noise Voltage vs C_{NR} in the *Typical Characteristics* section.

The TPS7A3701 adjustable version does not have the NR pin available. However, connecting a feedback capacitor, C_{FB} , from the output to the feedback pin (FB) reduces output noise and improve load transient performance. This capacitor should be limited to 0.1 μ F.

The TPS7A37 uses an internal charge pump to develop an internal supply voltage sufficient to drive the gate of the NMOS pass element above V_{OUT} . The charge pump generates ~250 µV of switching noise at ~4 MHz; however, charge-pump noise contribution is negligible at the output of the regulator for most values of I_{OUT} and C_{OUT} .



Application Information (continued)

8.1.3 Dropout Voltage

The TPS7A37 uses an NMOS pass transistor to achieve extremely low dropout. When $(V_{IN} - V_{OUT})$ is less than the dropout voltage (V_{DO}) , the NMOS pass device is in its linear region of operation and the input-to-output resistance is the R_{DS. ON} of the NMOS pass element.

For large step changes in load current, the TPS7A37 requires a larger voltage drop from V_{IN} to V_{OUT} to avoid degraded transient response. The boundary of this transient dropout region is approximately twice the dc dropout. Values of $V_{IN} - V_{OUT}$ above this line ensure normal transient response.

Operating in the transient dropout region can cause an increase in recovery time. The time required to recover from a load transient is a function of the magnitude of the change in load current rate, the rate of change in load current, and the available headroom (V_{IN} to V_{OUT} voltage drop). Under worst-case conditions [full-scale instantaneous load change with ($V_{IN} - V_{OUT}$) close to dc dropout levels], the TPS7A37 can take a couple of hundred microseconds to return to the specified regulation accuracy.

8.1.4 Transient Response

The low open-loop output impedance provided by the NMOS pass element in a voltage follower configuration allows operation without a $1.0-\mu$ F output capacitor. As with any regulator, the addition of additional capacitance from the OUT pin to ground reduces undershoot magnitude but increases its duration. In the adjustable version, the addition of a capacitor, C_{FB}, from the OUT pin to the FB pin will also improve the transient response.

The TPS7A37 does not have active pull-down when the output is over-voltage. This architecture allows applications that connect higher voltage sources, such as alternate power supplies, to the output. This architecture also results in an output overshoot of several percent if the load current quickly drops to zero when a capacitor is connected to the output. The duration of overshoot can be reduced by adding a load resistor. The overshoot decays at a rate determined by output capacitor C_{OUT} and the internal/external load resistance. The rate of decay is given by:

(Fixed voltage version)

$$\frac{dV}{dT} = \frac{V_{OUT}}{C_{OUT} \times 80 k\Omega \parallel R_{LOAD}}$$

(4)

(Adjustable voltage version)

$$\frac{dV}{dT} = \frac{V_{OUT}}{C_{OUT} \times 80 k\Omega \parallel (R_1 + R_2) \parallel R_{LOAD}}$$

(5)

TPS7A37 ZHCSB77B – MARCH 2013 – REVISED AUGUST 2015 Texas Instruments

www.ti.com.cn

8.2 Typical Applications

8.2.1 Typical Application Schematic

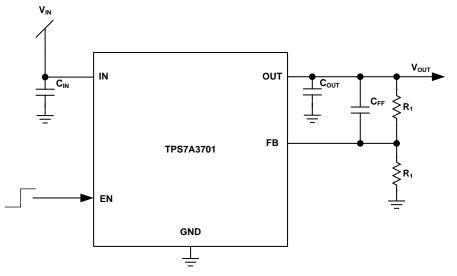


Figure 31. Typical Application Schematic

8.2.1.1 Design Requirements

Table 1 lists the design parameters.

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage	3.6 V
Output voltage	3.3 V
DC output current	100 mA
Peak output current	1 A

Table 1. Design Parameters

8.2.1.2 Detailed Design Procedure

Due to the transients in this application input and output capacitors should be used. A $C_{IN} = C_{OUT} = 10$ -uF capacitor has been selected.

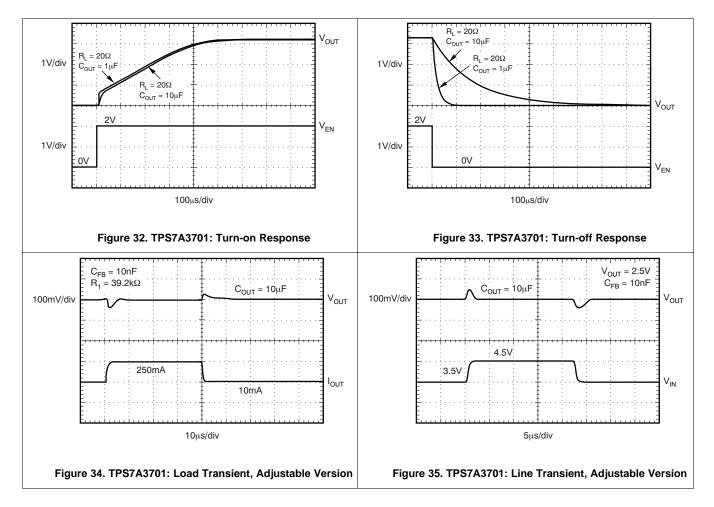
The ESR of the chosen capacitor can be checked by looking the magnitude of the complex impedance over frequency. When |Zc| reaches a minimum the DC ESR is the value of |Zc| at that frequency. The ESR of the chosen capacitor is 10 m Ω , which gives us a product of 10 m Ω * 10 uF = 100 n Ω -F > 50 n Ω -F, minimizing the ringing during transients.

As the V_{IN} - V_{OUT} change is only 300 mV with a 100-mA DC current, the expected junction temperature rise over the ambient, on a JEDEC standard board, is 67.2 C/W × 0.3V × 0.1 A = 2 C.

To ensure best accuracy, R1 = 52.3 k Ω and R2 = 30.1 k Ω , and a 10-nF C_{FF} is used to reduce output noise.



8.2.1.3 Application Curves



8.2.2 Fixed-Voltage Version

Figure 36 shows the basic circuit connections for the fixed voltage models.

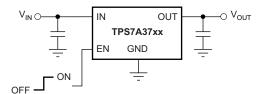


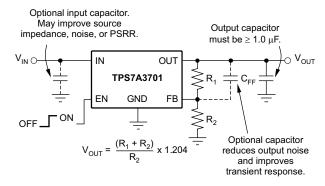
Figure 36. Typical Application Circuit for Fixed-Voltage Version

8.2.3 Adjustable Operation

Figure 37 gives the connections for the adjustable output version, TPS7A3701 ⁽¹⁾.

 R_1 and R_2 can be calculated for any output voltage using the formula shown in Figure 37. Sample resistor values for common output voltages are shown in Figure 30.

For best accuracy, make the parallel combination of R_1 and R_2 approximately equal to 19 k Ω . This 19 k Ω , in addition to the internal 8-k Ω resistor, presents the same impedance to the error amp as the 27-k Ω bandgap reference output. This impedance helps compensate for leakages into the error amp terminals.





(1) Product-preview device.



9 Power Supply Recommendations

The input supply for the LDO must be within its recommended operating conditions (that is, between 2.2 V to 5.5 V). The input voltage must provide adequate headroom in order for the device to have a regulated output. If the input supply is noisy, additional input capacitors with low ESR can help improve the output transient performance.

10 Layout

10.1 Layout Guidelines

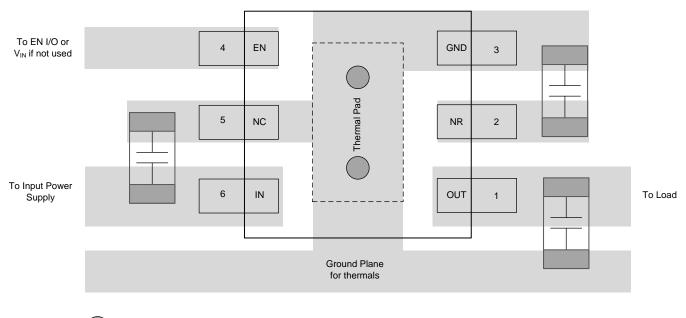
Layout is a critical part of good power-supply design. There are several signal paths that conduct fast-changing currents or voltages that can interact with stray inductance or parasitic capacitance to generate noise or degrade the power-supply performance. To help eliminate these problems, the IN pin should be bypassed to ground with a low ESR ceramic bypass capacitor with an X5R or X7R dielectric.

The GND pin should be tied directly to the PowerPAD under the IC. The PowerPAD should be connected to any internal PCB ground planes using multiple vias directly under the IC.

Do not place any of the capacitors on the opposite side of the PCB from where the regulator is installed. The use of vias and long traces is strongly discouraged because these circuits may impact system performance negatively, and even cause instability.

10.1.1 Board Layout Recommendations to Improve PSRR and Noise Performance

To improve AC performance (such as PSRR, output noise, and transient response), TI recommends designing the board with separate ground planes for V_{IN} and V_{OUT} , with each ground plane star connected only at the GND pin of the device.



10.2 Layout Example

*Denotes thermal vias for heat dissipation

Figure 38. Fixed Voltage Layout



Layout Example (continued)

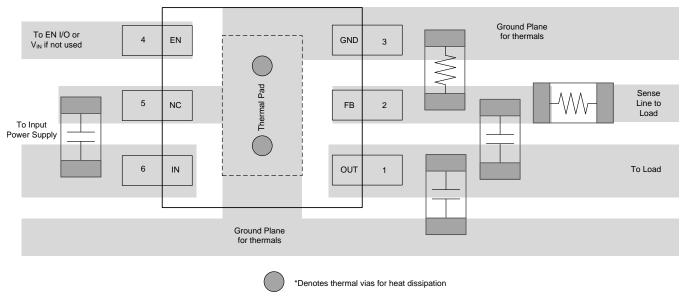


Figure 39. Adjustable Voltage Layout

10.3 Thermal Considerations

Thermal protection disables the output when the junction temperature rises to approximately +160°C, allowing the device to cool. When the junction temperature cools to approximately +140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits the dissipation of the regulator, protecting it from damage due to overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature should be limited to +125°C maximum. To estimate the margin of safety in a complete design (including heatsink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, thermal protection should trigger at least +35°C above the maximum expected ambient condition of your application. This produces a worst-case junction temperature of +125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS7A37 has been designed to protect against overload conditions. It was not intended to replace proper heatsinking. Continuously running the TPS7A37 into thermal shutdown degrades device reliability.

10.4 Power Dissipation

Knowing the device power dissipation and proper sizing of the thermal plane that is connected to the tab or pad is critical to avoiding thermal shutdown and ensuring reliable operation.

Power dissipation of the device depends on input voltage and load conditions and can be calculated using Equation 6:

$$P_{D} = (V_{IN} - V_{OUT}) \times I_{OUT}$$

Power dissipation can be minimized and greater efficiency can be achieved by using the lowest possible input voltage necessary to achieve the required output voltage regulation.

(6)



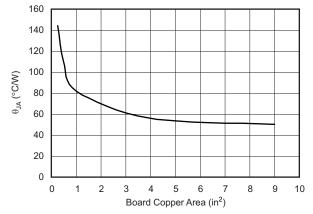
Power Dissipation (continued)

On the WSON (DRV) package, the primary conduction path for heat is through the exposed pad to the printed circuit board (PCB). The pad can be connected to ground or be left floating; however, it should be attached to an appropriate amount of copper PCB area to ensure the device does not overheat. That tab should be connected to ground. The maximum junction-to-ambient thermal resistance depends on the maximum ambient temperature, maximum device junction temperature, and power dissipation of the device and can be calculated using Equation 7:

$$\mathsf{R}_{\theta \mathsf{J}\mathsf{A}} = \frac{\left(+125^{\circ}\mathsf{C} - \mathsf{T}_{\mathsf{A}}\right)}{\mathsf{P}_{\mathsf{D}}}$$

(7)

Knowing the maximum $R_{\theta JA}$, the minimum amount of PCB copper area needed for appropriate heatsinking can be estimated using Figure 40.



Note: θ_{JA} value at board size of $9in^2$ (that is, $3in \times 3in$) is a JEDEC standard.



Figure 40 shows the variation of θ_{JA} as a function of ground plane copper area in the board. It is intended only as a guideline to demonstrate the effects of heat spreading in the ground plane and should not be used to estimate actual thermal performance in real application environments.

NOTE

When the device is mounted on an application PCB, it is strongly recommended to use Ψ_{JT} and Ψ_{JB} , as explained in the *Estimating Junction Temperature* section.

10.5 Estimating Junction Temperature

Using the thermal metrics Ψ_{JT} and Ψ_{JB} , as shown in the *Thermal Information* table, the junction temperature can be estimated with corresponding formulas (given in Equation 8). For backwards compatibility, an older θ_{JC} , *Top* parameter is listed as well.

$$\Psi_{\mathsf{JT}}: \quad \mathsf{T}_{\mathsf{J}} = \mathsf{T}_{\mathsf{T}} + \Psi_{\mathsf{JT}} \bullet \mathsf{P}_{\mathsf{D}}$$

$$\Psi_{\mathsf{JB}}: \quad \mathsf{T}_{\mathsf{J}} = \mathsf{T}_{\mathsf{B}} + \Psi_{\mathsf{JB}} \bullet \mathsf{P}_{\mathsf{D}}$$

(8)

Where P_D is the power dissipation shown by Equation 6, T_T is the temperature at the center-top of the IC package, and T_B is the PCB temperature measured 1mm away from the IC package *on the PCB surface* (as Figure 42 shows).

NOTE

Both T_T and T_B can be measured on actual application boards using a thermo-gun (an infrared thermometer).



Estimating Junction Temperature (continued)

35 30 25

20

15 10 5

Ψ_{JT} and Ψ_{JB} (°C/W)

For more information about measuring T_T and T_B , see the application note SBVA025, Using New Thermal Metrics, available for download at www.ti.com.

By looking at Figure 41, the new thermal metrics (Ψ_{JT} and Ψ_{JB}) have very little dependency on board size. That is, using Ψ_{JT} or Ψ_{JB} with Equation 8 is a good way to estimate T_J by simply measuring T_T or T_B , regardless of the application board size.

 $\mathsf{DRV}\ \Psi_{\mathsf{JB}}$

 $\Psi_{\rm JT}$

-- DRV

T_T on top

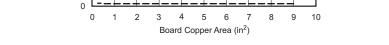
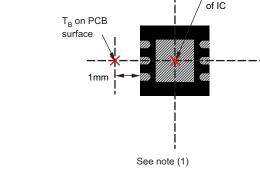


Figure 41. DRV (WSON) Package Ψ_{JT} and Ψ_{JB} vs Board Size

For a more detailed discussion of why TI does not recommend using $\theta_{JC(top)}$ to determine thermal characteristics, refer to application report SBVA025, *Using New Thermal Metrics*, available for download at www.ti.com. For further information, refer to application report SPRA953, *Semiconductor and IC Package Thermal Metrics*, also available on the TI website.



(1) Power dissipation may limit operating range. Check *Thermal Information* table.

(2) Example DRV (SON) Package Measurement

Figure 42. Measuring Points for $T_{\rm T}$ and $T_{\rm B}$





11 器件和文档支持

- 11.1 文档支持
- 11.1.1 相关文档
- 《使用新的热指标》, SBVA025
- 《TPS7A37xxEVM-529 评估模块》, SLVU850

11.1.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

- TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.
- **Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.2 商标

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

11.3 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

11.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对 本文档进行修订的情况下发生改变。要获得这份数据表的浏览器版本,请查阅左侧的导航栏。



PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
TPS7A3701DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SJI	Samples
TPS7A3701DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SJI	Samples
TPS7A3721DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SIX	Samples
TPS7A3721DRVT	ACTIVE	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SIX	Samples
TPS7A3725DRVR	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SJH	Samples
TPS7A3725DRVT	LIFEBUY	WSON	DRV	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	SJH	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



www.ti.com

PACKAGE OPTION ADDENDUM

24-Aug-2023

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS7A3701DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS7A3701DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS7A3721DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS7A3721DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS7A3725DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS7A3725DRVT	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

5-Jan-2021



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS7A3701DRVR	WSON	DRV	6	3000	213.0	191.0	35.0
TPS7A3701DRVT	WSON	DRV	6	250	213.0	191.0	35.0
TPS7A3721DRVR	WSON	DRV	6	3000	213.0	191.0	35.0
TPS7A3721DRVT	WSON	DRV	6	250	213.0	191.0	35.0
TPS7A3725DRVR	WSON	DRV	6	3000	213.0	191.0	35.0
TPS7A3725DRVT	WSON	DRV	6	250	213.0	191.0	35.0

DRV 6

GENERIC PACKAGE VIEW

WSON - 0.8 mm max height PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



DRV0006D



PACKAGE OUTLINE

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



DRV0006D

EXAMPLE BOARD LAYOUT

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



DRV0006D

EXAMPLE STENCIL DESIGN

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



重要声明和免责声明

TI"按原样"提供技术和可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源, 不保证没有瑕疵且不做出任何明示或暗示的担保,包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担 保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任:(1) 针对您的应用选择合适的 TI 产品,(2) 设计、验 证并测试您的应用,(3) 确保您的应用满足相应标准以及任何其他功能安全、信息安全、监管或其他要求。

这些资源如有变更,恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。 您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成的任何索赔、损害、成 本、损失和债务,TI 对此概不负责。

TI 提供的产品受 TI 的销售条款或 ti.com 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

TI 反对并拒绝您可能提出的任何其他或不同的条款。

邮寄地址:Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2023,德州仪器 (TI) 公司